

2813



SONNENSCHN, NATH & ROSENTHAL

8000 Sears Tower
233 S. Wacker Drive
Chicago, IL 60606
312/876-0200

APPLICANTS: Fumihiko Nakamura et al. ATTY DOCKET NO: 09792909-5122
SERIAL NO.: 09/925,153 GROUP ART UNIT: 2813
DATE FILED: August 8, 2001 EXAMINER: David Blum
INVENTION: "INSULATING NITRIDE LAYER AND PROCESS FOR ITS FORMING, AND SEMICONDUCTOR DEVICE AND PROCESS FOR ITS PRODUCTION"

AMENDMENT "C"

Hon. Assistant Commissioner of Patents
Washington D.C. 2023

SIR:

Transmitted herewith is an amendment in the above-identified application.

Additional claim fee is required.

The fee has been calculated as shown below.

CLAIMS AS AMENDED						
	(2) CLAIMS REMAINING AFTER AMENDMENT		(4) HIGHEST NO. PREVIOUSLY PAID FOR	(5) PRESENT EXTRA	(6) RATE	(7) ADDITIONAL FEE
TOTAL CLAIMS		MINUS	20	0	() X 9.00 () X 18.00	0.00
INDEP. CLAIMS		MINUS	3	0	() X 39.00 () X 84.00	0.00
Application amended to contain any multiple dependent claims not previously paid for.				() YES (X) NO	() \$135.00 () \$270.00 ONE TIME	
				TOTAL ADDITIONAL FEE FOR THIS AMENDMENT		\$0.00

- Applicant petitions the Commissioner of Patents and Trademarks to extend this time for response to the Office Action dated _____ for _____ month so that the period for response is extended to _____.
- A check in the amount of \$ _____ is attached to cover the extension of time fee.
- A check in the amount of \$ _____ is attached to cover the additional claim fee.
- ☒ The Commissioner is hereby authorized to charge any additional fees which may be required, or to credit any overpayment to account No. 19-3140. A duplicate of this sheet is enclosed.
- When phoning re this application, please call 312/876-8000 - Ext. 2606.

SONNENSCHN NATH & ROSENTHAL

DATE: September 6, 2002BY Christopher P. Rauch (Reg. No. 45,034)
Christopher P. Rauch

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited as first class mail in an envelope addressed to Asst. Commissioner of Patents, Washington, D.C. 20231 on September 6, 2002.

Christopher P. Rauch
Christopher P. Rauch

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SEP 20 2002
TECHNOLOGY CENTER 2800

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9-27-2
Robert
Amelt



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Hon. Assistant Commissioner for Patents
Washington, DC 20231

S I R:

This Amendment "C" is filed in response to the Office Action of June 7, 2002. Please reconsider the application in view of the amendment and remarks presented below.

IN THE DRAWINGS

Please amend Figures 12, 13, and 14 as indicated on the drawing sheet marked in red submitted with the Request for Approval of Drawing Changes submitted herewith.

IN THE CLAIMS

Please amend claims 1 and 13 as follows:

A1 SUB B1 1. (Amended) An insulating nitride layer formed from a group III-V nitride compound semiconductor heavily doped mostly with cadmium.

A2 SUB B4 13. (Amended) A semiconductor device which has an insulating nitride layer formed from a group III-V nitride compound semiconductor heavily doped mostly with cadmium.

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